

R-C Thermal Model Parameters

DESCRIPTION

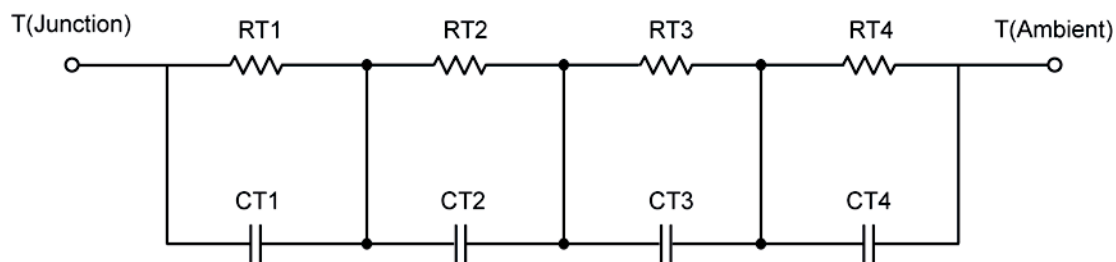
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

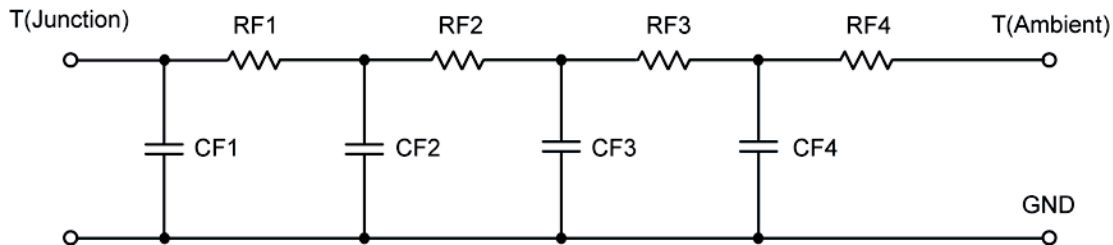
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	13.1726	N/A	6.5039
RT2	22.4447	N/A	19.9984
RT3	34.3423	N/A	10.9885
RT4	55.0404	N/A	7.5092
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	342.8128 u	N/A	150.1013 m
CT2	61.3646 m	N/A	1.7193 m
CT3	3.4091 m	N/A	6.1462 m
CT4	1.3732	N/A	196.8209 u

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	16.0347	N/A	8.7965
RF2	36.7512	N/A	29.5268
RF3	20.6145	N/A	2.1542
RF4	51.5996	N/A	4.5225
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	312.5484 u	N/A	154.7457 u
CF2	3.1565 m	N/A	1.2134 m
CF3	83.1170 m	N/A	120.3345 m
CF4	1.4144	N/A	665.7070 u

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

